				Time at amp
		``••	DB	Time stamp
		11-00%	USPAT;	2002/11/14 19:47
L Number	1 1	Search Text (irradiat\$3 heat\$3 anneal\$3) near10 (laser near5 light) near10 air near10 crystal\$6 (irradiat\$3 heat\$3 anneal\$3) near10 (laser (irradiat\$3 heat\$3 anneal\$3) air near10 crystal\$6	US-PGPUB USPAT	2002/11/14 19:41
4	1	(irradiats) neary mear 10 crystals6	USPAT;	2002/11/14 19:48
8	129	near5 light) near10 all hear100 (irradiat\$3 heat\$3 anneal\$3) near100 (laser near5 light) near100 air (irradiat\$3 heat\$3 anneal\$3) near10 (laser	US-PGPUB USPAT; US-PGPUB	2002/11/14 20:01
9	86	(irradiats3 heat;3 dimensionals3) near10	USPAT; US-PGPUB	2002/11/14 20:02
10	10	(laser nears light, a transistor))		2002/11/14 20:02
11	81	(irradiat\$3 heat\$3 annear\$7 near5 light) near10 air	DERWENT; IBM_TDB EPO; JPO;	2002/11/14 20:02
12	1	((irradiat\$3 heat\$3 anneal\$3) near10 (laser near5 light) near10 air) and (TFT (thin near2 film near2 transistor))	DERWENT; IBM TDB	

Page 1